

**Notice of References Cited**

Application/Control No.

10/573,458

Applicant(s)/Patent Under

Reexamination

OTSUKA ET AL.

Examiner

Christopher M. Roland

Art Unit

2893

Page 1 of 2

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*	Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a))  
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